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FSDM0465RB

Green Mode Fairchild Power Switch (FPS™)

Features

- Internal Avalanche Rugged SenseFET
- Advanced Burst-Mode Operation Consumes Under One W at 240VAC & 0.5W Load
- Precision Fixed Operating Frequency (66kHz)
- Internal Start-up Circuit
- Improved Pulse by Pulse Current Limiting
- Over Voltage Protection (OVP) : Auto-Restart
- Over Load Protection (OLP): Auto-Restart
- Internal Thermal Shutdown (TSD) : Auto-Restart
- Under Voltage Lock Out (UVLO) with Hysteresis
- Low Operating Current (2.5mA)
- Built-in Soft Start

Application

- SMPS for LCD monitor and STB
- Adapter

Related Application Notes

- **AN4137** - Design Guidelines for Off-line Flyback Converters Using Fairchild Power Switch (FPS)
- **AN4140** - Transformer Design Consideration for Off-line Flyback Converters Using Fairchild Power Switch
- **AN4141** - Troubleshooting and Design Tips for Fairchild Power Switch Flyback Applications
- **AN4148** - Audible Noise Reduction Techniques for FPS Applications

Description

The FSDM0465RB is an integrated Pulse Width Modulator (PWM) and SenseFET specifically designed for high performance offline Switch Mode Power Supplies (SMPS) with minimal external components. This device is an integrated high voltage power switching regulator which combines a rugged avalanche, SenseFET with a current mode PWM control block. The PWM controller includes integrated fixed frequency oscillator, under voltage lockout, leading edge blanking (LEB), optimized gate driver, internal soft start, temperature compensated precise current sources for a loop compensation and self protection circuitry. Compared with a discrete MOSFET and PWM controller solution, the PWM/FSDMRB can reduce total cost, component count, size and weigh, while simultaneously increasing efficiency, productivity, and system reliability. This device provides a basic platform well suited for cost-effective designs of flyback converters.

| OUTPUT POWER TABLE (4) | | | | |
|------------------------|----------------------------|---------------------------|-------------------------|---------------------------|
| PRODUCT | 230VAC ±15% ⁽³⁾ | | 85-265VAC | |
| | Adapt-er ⁽¹⁾ | Open Frame ⁽²⁾ | Adapt-er ⁽¹⁾ | Open Frame ⁽²⁾ |
| FSDM0465RB | 48W | 56W | 40W | 48W |
| FSDM0565RB | 60W | 70W | 50W | 60W |
| FSDM07652RB | 70W | 80W | 60W | 70W |
| FSDM12652RB | 90W | 110W | 80W | 90W |

Table 1. Maximum Output Power

Notes:

1. Typical continuous power in a non-ventilated enclosed adapter measured at 50°C ambient.
2. Maximum practical continuous power in an open frame design at 50°C ambient.
3. 230 VAC or 100/115 VAC with doubler.
4. The junction temperature can limit the maximum output power.

Typical Circuit

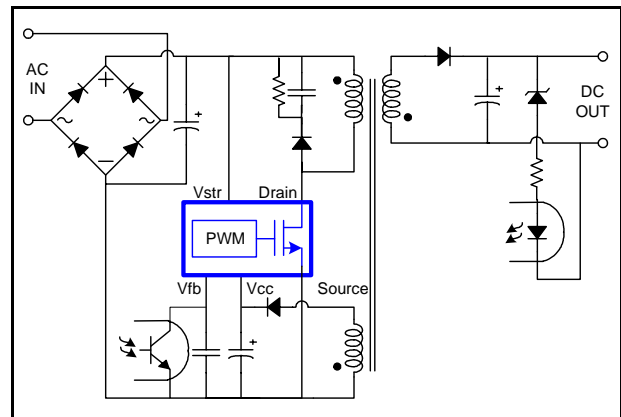


Figure 1. Typical Flyback Application

Internal Block Diagram

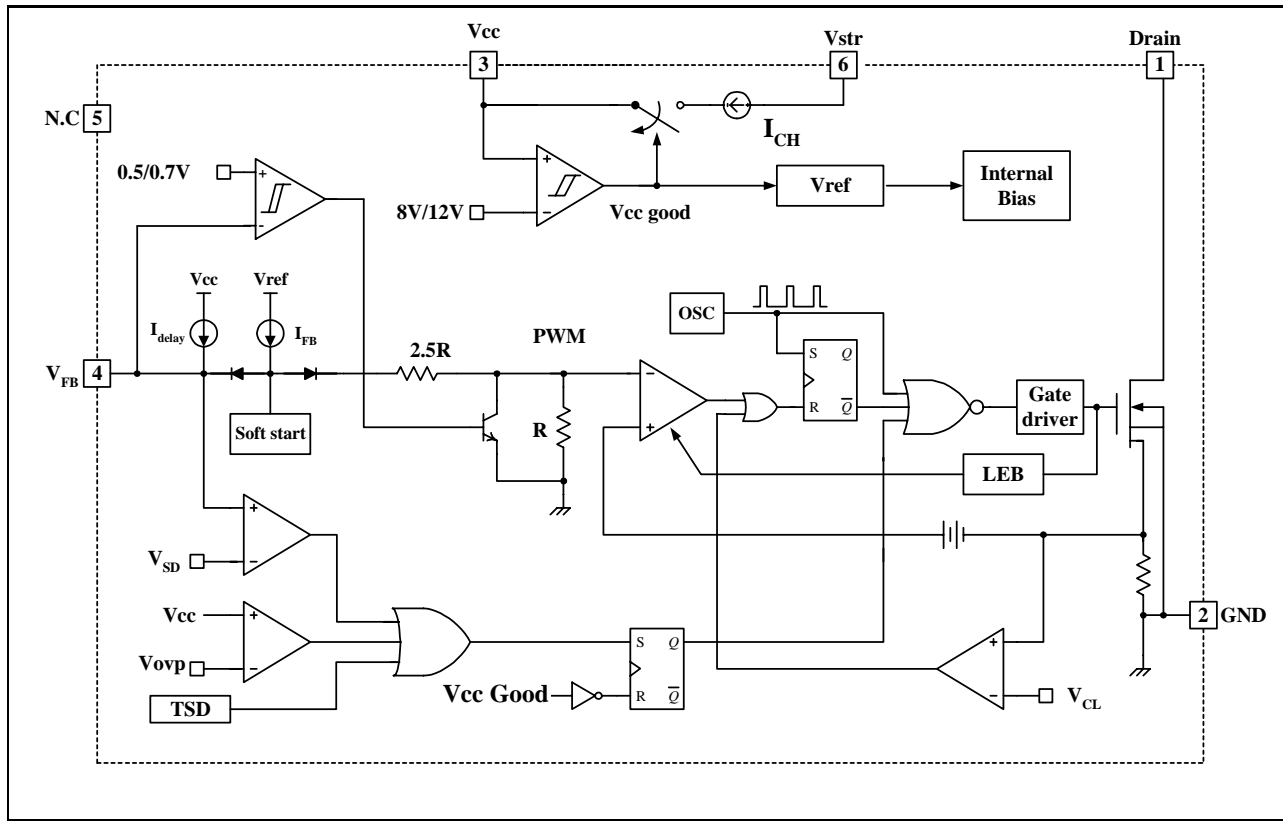


Figure 2. Functional Block Diagram of FSDM0465RB

Pin Description

| Pin Number | Pin Name | Pin Function Description |
|------------|----------|---|
| 1 | Drain | This pin is the high voltage power SenseFET drain. It is designed to drive the transformer directly. |
| 2 | GND | This pin is the control ground and the SenseFET source. |
| 3 | Vcc | This pin is the positive supply voltage input. During start up, the power is supplied by an internal high voltage current source that is connected to the Vstr pin. When Vcc reaches 12V, the internal high voltage current source is disabled and the power is supplied from the auxiliary transformer winding. |
| 4 | Vfb | This pin is internally connected to the inverting input of the PWM comparator. The collector of an opto-coupler is typically tied to this pin. For stable operation, a capacitor should be placed between this pin and GND. If the voltage of this pin reaches 6.0V, the over load protection is activated resulting in shutdown of the FPS™. |
| 5 | N.C | - |
| 6 | Vstr | This pin is connected directly to the high voltage DC link. At startup, the internal high voltage current source supplies internal bias and charges the external capacitor that is connected to the Vcc pin. Once Vcc reaches 12V, the internal current source is disabled. |

Pin Assignments

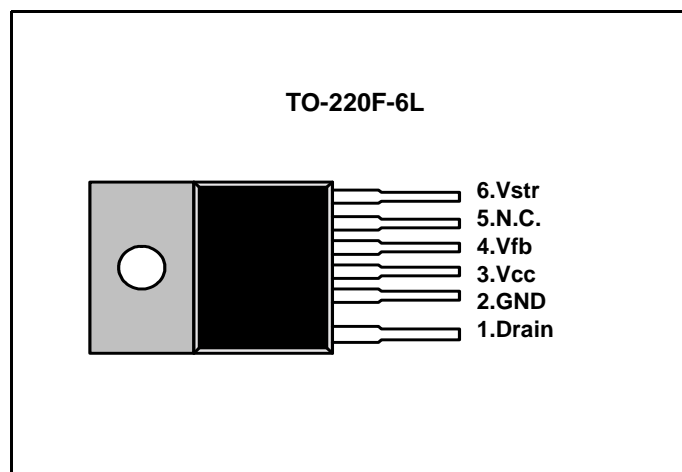


Figure 3. Pin Configuration (Top View)

Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---|------------------|---|---------|
| Drain-source Voltage | V _{DSS} | 650 | V |
| V _{str} Max Voltage | V _{STR} | 650 | V |
| Pulsed Drain Current (T _c =25°C) ⁽¹⁾ | I _{DM} | 9.6 | A |
| Continuous Drain Current (T _c =25°C) ⁽²⁾ | I _D | 2.2 | A (rms) |
| Continuous Drain Current (T _c =100°C) ⁽²⁾ | | 1.4 | A (rms) |
| Continuous Drain Current* (T _{DL} =25°C) ⁽³⁾ | I _D * | 4 | A (rms) |
| Single Pulsed Avalanche Energy ⁽⁴⁾ | E _{AS} | - | mJ |
| Supply Voltage | V _{CC} | 20 | V |
| Input Voltage Range | V _{FB} | -0.3 to V _{CC} | V |
| Total Power Dissipation (T _c =25°C) ⁽²⁾ | P _D | 33 | W |
| Operating Junction Temperature | T _j | Internally limited | °C |
| Operating Ambient Temperature | T _A | -25 to +85 | °C |
| Storage Temperature Range | T _{STG} | -55 to +150 | °C |
| ESD Capability, HBM Model (All pins except V _{str} and V _{fb}) | - | 2.0 (GND-V _{str} /V _{fb} =1.5kV) | kV |
| ESD Capability, Machine Model (All pins except V _{str} and V _{fb}) | - | 300 (GND-V _{str} /V _{fb} =225V) | V |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. T_c: Case Back Surface Temperature (With infinite heat sink)
3. T_{DL}: Drain Lead Temperature (With infinite heat sink)
4. L=14mH, starting T_j=25°C. L=14mH, starting T_j=25°C

Thermal Impedance

| Parameter | Symbol | Value | Unit |
|-----------------------------|--------------------------------|-------|------|
| Junction-to-Ambient Thermal | θ _{JA} | - | °C/W |
| Junction-to-Case Thermal | θ _{JC} ⁽¹⁾ | 3.78 | °C/W |

Notes:

1. Infinite cooling condition - refer to the SEMI G30-88.

Electrical Characteristics

(Ta = 25°C unless otherwise specified)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--|---------|------------------------------------|------|------|------|------|
| SenseFET SECTION | | | | | | |
| Drain Source Breakdown Voltage | BVDSS | VGS = 0V, ID = 250μA | 650 | - | - | V |
| Zero Gate Voltage Drain Current | IDSS | VDS = 650V, VGS = 0V | - | - | 250 | μA |
| | | VDS = 520V VGS = 0V, TC = 125°C | - | - | 250 | μA |
| Static Drain Source On Resistance ⁽¹⁾ | RDS(ON) | VGS = 10V, ID = 2.5A | - | 2.2 | 2.6 | Ω |
| Output Capacitance | COSS | VGS = 0V, VDS = 25V, f = 1MHz | - | 60 | - | pF |
| Turn On Delay Time | TD(ON) | VDD = 325V, ID = 3.2A | - | 23 | - | ns |
| Rise Time | TR | | - | 20 | - | |
| Turn Off Delay Time | TD(OFF) | | - | 65 | - | |
| Fall Time | TF | | - | 27 | - | |
| CONTROL SECTION | | | | | | |
| Initial Frequency | FOSC | VFB = 3V | 60 | 66 | 72 | kHz |
| Voltage Stability | FSTABLE | 13V ≤ VCC ≤ 18V | 0 | 1 | 3 | % |
| Temperature Stability ⁽²⁾ | ΔFOSC | -25°C ≤ Ta ≤ 85°C | 0 | ±5 | ±10 | % |
| Maximum Duty Cycle | DMAX | - | 77 | 82 | 87 | % |
| Minimum Duty Cycle | DMIN | - | - | - | 0 | % |
| Start Threshold Voltage | VSTART | VFB=GND | 11 | 12 | 13 | V |
| Stop Threshold Voltage | VSTOP | VFB=GND | 7 | 8 | 9 | V |
| Feedback Source Current | IFB | VFB=GND | 0.7 | 0.9 | 1.1 | mA |
| Soft-start Time | TS | Vfb=3 | - | 10 | 15 | ms |
| Leading Edge Blanking Time | TLEB | - | - | 250 | - | ns |
| BURST MODE SECTION | | | | | | |
| Burst Mode Voltages | VBURH | VCC=14V | - | 0.7 | - | V |
| | VBURL | VCC=14V | - | 0.5 | - | V |

Electrical Characteristics (Continued)

(Ta = 25°C unless otherwise specified)

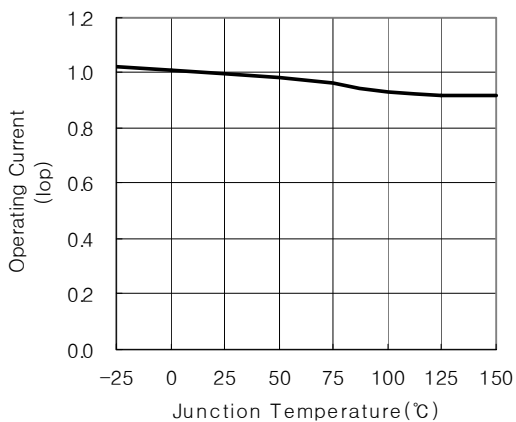
| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|---|----------------------|--|------|------|------|------|
| PROTECTION SECTION | | | | | | |
| Peak Current Limit ⁽³⁾ | I _{OVER} | V _{FB} =5V, V _{CC} =14V | 1.6 | 1.8 | 2.0 | A |
| Over Voltage Protection | V _{OVP} | - | 18 | 19 | 20 | V |
| Thermal Shutdown Temperature ⁽²⁾ | T _{SD} | - | 130 | 145 | 160 | °C |
| Shutdown Feedback Voltage | V _{SD} | V _{FB} ≥ 5.5V | 5.5 | 6.0 | 6.5 | V |
| Shutdown Delay Current | I _{DELAY} | V _{FB} =5V | 2.8 | 3.5 | 4.2 | μA |
| TOTAL DEVICE SECTION | | | | | | |
| Startup Current ⁽⁴⁾ | I _{start} | V _{FB} =GND, V _{CC} =11V | - | 1 | 1.3 | mA |
| Operating Supply Current ⁽⁴⁾ | I _{OP} | V _{FB} =GND, V _{CC} =14V | - | 2.5 | 5 | mA |
| | I _{OP(MIN)} | V _{FB} =GND, V _{CC} =10V | | | | |
| | I _{OP(MAX)} | V _{FB} =GND, V _{CC} =18V | | | | |

Notes:

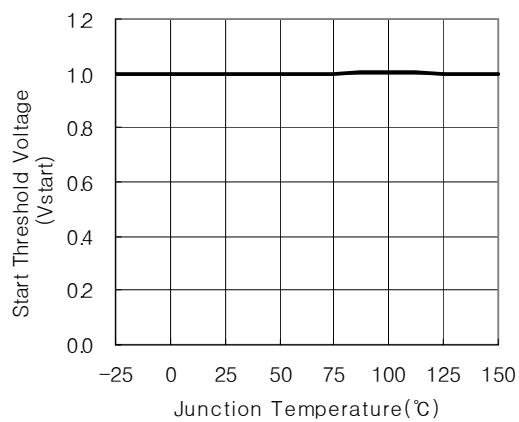
1. Pulse test: Pulse width ≤ 300μS, duty ≤ 2%
2. These parameters, although guaranteed at the design, are not tested in mass production.
3. These parameters indicate the inductor current.
4. This parameter is the current flowing into the control IC.

Typical Performance Characteristics

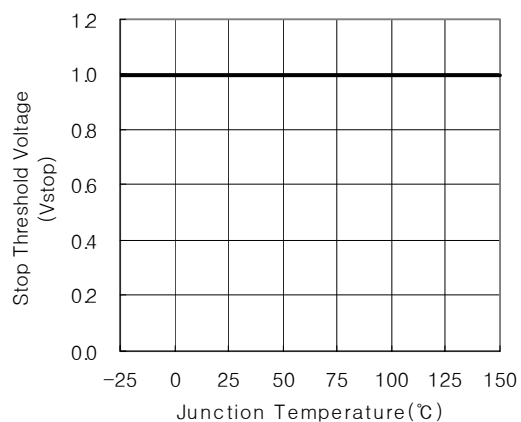
(These Characteristic Graphs are Normalized at Ta= 25°C)



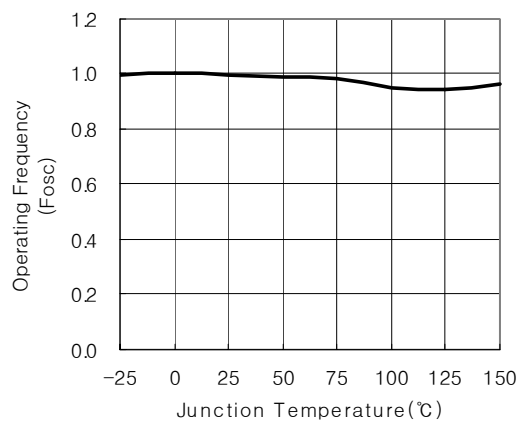
Operating Current vs. Temp



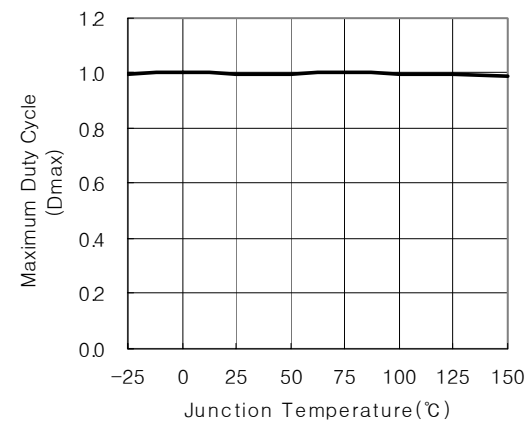
Start Threshold Voltage vs. Temp



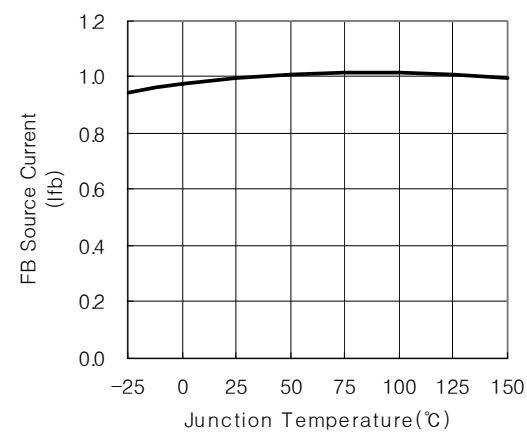
Stop Threshold Voltage vs. Temp



Operating Frequency vs. Temp



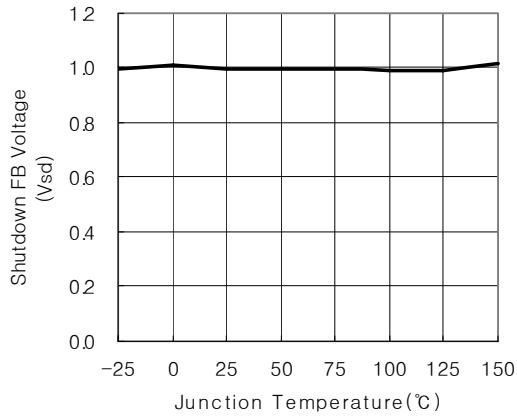
Maximum Duty vs. Temp



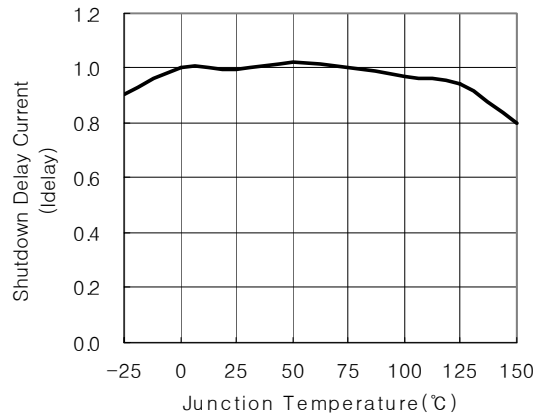
Feedback Source Current vs. Temp

Typical Performance Characteristics (Continued)

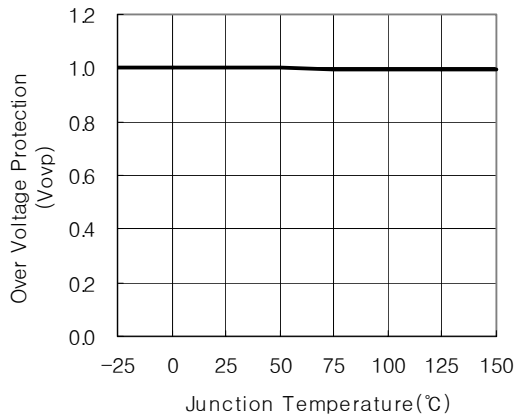
(These Characteristic Graphs are Normalized at Ta= 25°C)



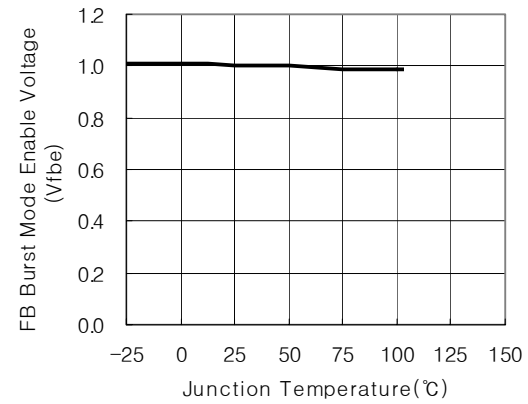
Shutdown Feedback Voltage vs. Temp



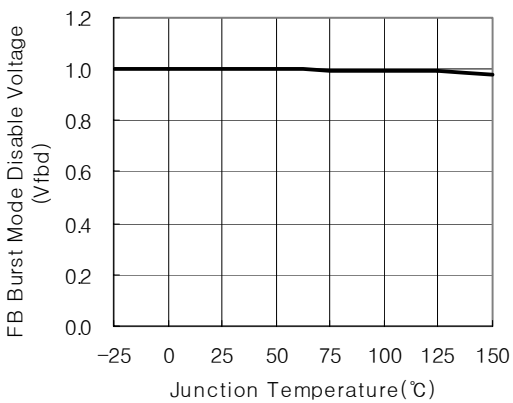
Shutdown Delay Current vs. Temp



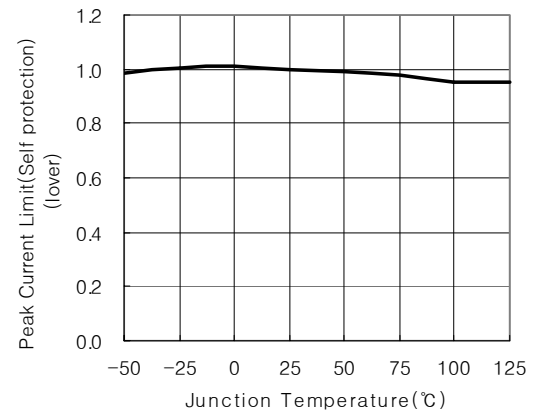
Over Voltage Protection vs. Temp



Burst Mode Enable Voltage vs. Temp



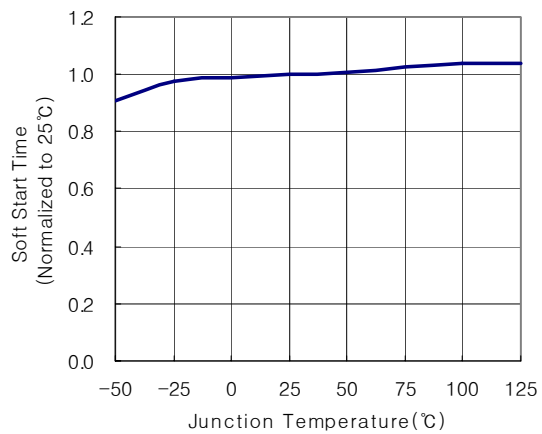
Burst Mode Disable Voltage vs. Temp



Current Limit vs. Temp

Typical Performance Characteristics (Continued)

(These Characteristic Graphs are Normalized at Ta= 25°C)



Soft Start Time vs. Temp

Functional Description

1. Startup: In previous generations of Fairchild Power Switches (FPS™) the Vcc pin had an external start-up resistor to the DC input voltage line. In this generation the startup resistor is replaced by an internal high voltage current source. At startup, an internal high voltage current source supplies the internal bias and charges the external capacitor (C_a) that is connected to the Vcc pin as illustrated in Figure 4. When Vcc reaches 12V, the FSDM0465RB begins switching and the internal high voltage current source is disabled. Then, the FSDM0465RB continues its normal switching operation and the power is supplied from the auxiliary transformer winding unless Vcc goes below the stop voltage of 8V.

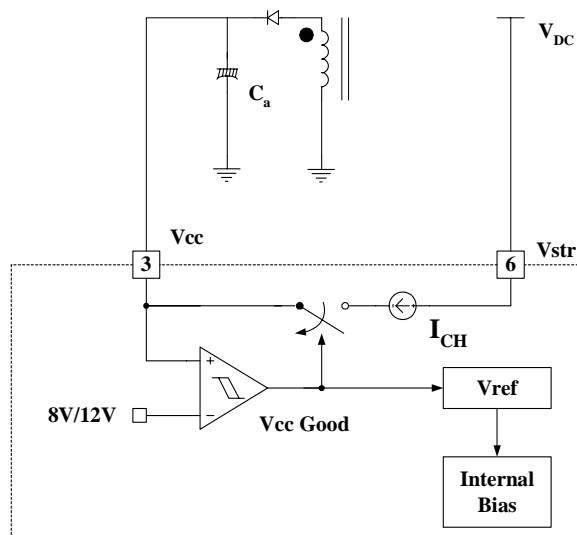


Figure 4. Internal Startup Circuit

2. Feedback Control: FSDM0465RB employs current mode control, as shown in Figure 5. An opto-coupler (such as the H11A817A) and shunt regulator (such as the KA431) are typically used to implement the feedback network. Comparing the feedback voltage with the voltage across the R_{sense} resistor plus an offset voltage makes it possible to control the switching duty cycle. When the reference pin voltage of the KA431 exceeds the internal reference voltage of 2.5V, the H11A817A LED current increases, thus decreasing the feedback voltage and reducing the duty cycle. This event typically happens when the input voltage is increased or the output load is decreased.

2.1 Pulse-by-Pulse Current Limit: Because current mode control is employed, the peak current through the SenseFET is limited by the inverting input of the PWM comparator (Vfb*) as shown in Figure 5. Assuming that the 0.9mA current source flows only through the internal resistor (2.5R + R = 2.8 kΩ), the cathode voltage of diode D2 is about 2.5V. Since D1 is blocked when the feedback voltage (Vfb) exceeds 2.5V, the maximum voltage of the cathode of D2 is clamped at this voltage, thus clamping Vfb*. Therefore, the peak value of the current through the SenseFET is limited.

2.2 Leading Edge Blanking (LEB): At the instant the internal SenseFET is turned on, there usually exists a high current spike through the SenseFET, caused by primary-side capacitance and secondary-side rectifier reverse recovery. Excessive voltage across the R_{sense} resistor would lead to incorrect feedback operation in the current mode PWM control. To counter this effect, the FSDM0465RB employs an LEB circuit. This circuit inhibits the PWM comparator for a short time (T_{LEB}) after the SenseFET is turned on.

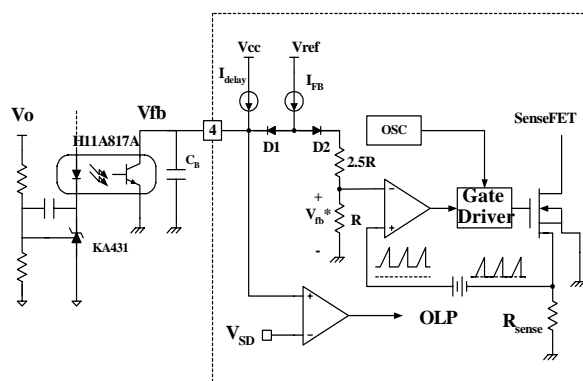


Figure 5. Pulse Width Modulation (PWM) Circuit

3. Protection Circuit: The FSDM0465RB has several self protective functions such as over load protection (OLP), over voltage protection (OVP), and thermal shutdown (TSD). Because these protection circuits are fully integrated into the IC without external components, the reliability can be improved without increasing cost. Once the fault condition occurs, switching is terminated and the SenseFET remains off. This causes Vcc to fall. When Vcc reaches the UVLO stop voltage, 8V, the protection is reset and the internal high voltage current source charges the Vcc capacitor via the Vstr pin. When Vcc reaches the UVLO start voltage, 12V, the FSDM0465RB resumes its normal operation. In this manner, the auto-restart can alternately enable and disable the switching of the power Sense FET until the fault condition is eliminated (see Figure 6).

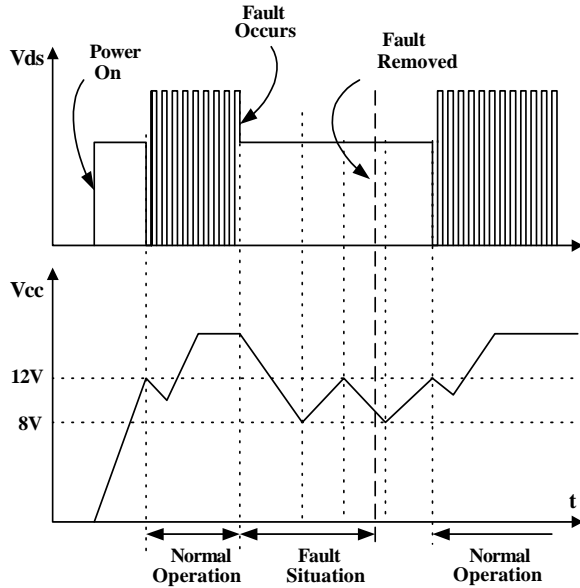


Figure 6. Auto Restart Operation

3.1 Over Load Protection (OLP): Overload is defined as the load current exceeding a pre-set level due to an unexpected event. In this situation, the protection circuit should be activated to protect the SMPS.

However, even when the SMPS is operation normally, the over load protection circuit can be activated during the load transition. To avoid this undesired operation, the over load protection circuit is designed to be activated after a specified time to determine whether it is a transient situation or an overload situation.

Because of the pulse-by-pulse current limit capability, the maximum peak current through the SenseFET is limited, and therefore the maximum input power is restricted with a given input voltage. If the output consumes beyond this maximum power, the output voltage (V_o) decreases below the set voltage. This reduces the current through the opto-coupler LED, which also reduces the opto-coupler transistor current, thus increasing the feedback voltage (V_{fb}).

If V_{fb} exceeds 2.5V, D1 is blocked and the 3.5uA current source starts to charge C_B slowly up to V_{cc} .

In this condition, V_{fb} continues increasing until it reaches 6V, when the switching operation is terminated as shown in Figure 7. The delay time for shutdown is the time required to charge C_B from 2.5V to 6.0V with 3.5uA.

In general, a 10 ~ 50 ms delay time is typical for most applications.

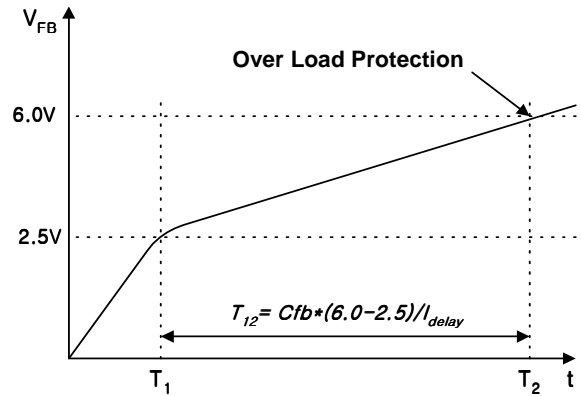


Figure 7. Over Load Protection

3.2 Over Voltage Protection (OVP): If the secondary side feedback circuit malfunction or a solder defect caused an open in the feedback path, the current through the opto-coupler transistor becomes almost zero. Then, V_{fb} climbs up in a similar manner to the over load situation, forcing the preset maximum current to be supplied to the SMPS until the over load protection is activated. Because more energy than required is provided to the output, the output voltage may exceed the rated voltage before the over load protection is activated, resulting in the breakdown of the devices in the secondary side. To prevent this situation, an OVP circuit is employed. In general, V_{cc} is proportional to the output voltage and the FSDM0465RB uses V_{cc} instead of directly monitoring the output voltage. If V_{cc} exceeds 19V, an OVP circuit is activated resulting in the termination of the switching operation. To avoid undesired activation of OVP during normal operation, V_{cc} should be designed to be below 19V.

3.3 Thermal Shutdown (TSD): The SenseFET and the control IC are built in one package. This makes it easy for the control IC to detect the heat generation from the Sense FET. When the temperature exceeds approximately 150°C, the thermal shutdown is activated.

4. Soft Start: The FSDM0465RB's internal soft-start circuit slowly increases the PWM comparator's inverting input voltage along with the SenseFET current after it starts up. The typical soft-start time is 10msec. The pulse width to the power switching device is progressively increased to establish the correct working conditions for transformers, inductors, and capacitors. The voltage on the output capacitors is progressively increased with the intention of smoothly establishing the required output voltage. It also helps to prevent transformer saturation and reduce the stress on the secondary diode during startup.

5. Burst Operation: To minimize power dissipation in standby mode, the FSDM0465RB enters burst mode operation. As the load decreases, the feedback voltage decreases. As shown in Figure 8, the device automatically enters burst mode when the feedback voltage drops below V_{BURL} (500mV). At this point switching stops and the output voltages start to drop at a rate dependent on the standby current load. This causes the feedback voltage to rise. Once it passes V_{BURH} (700mV), switching resumes. The feedback voltage then falls and the process repeats. Burst mode operation alternately enables and disables switching of the power SenseFET thereby reducing switching loss in Standby mode.

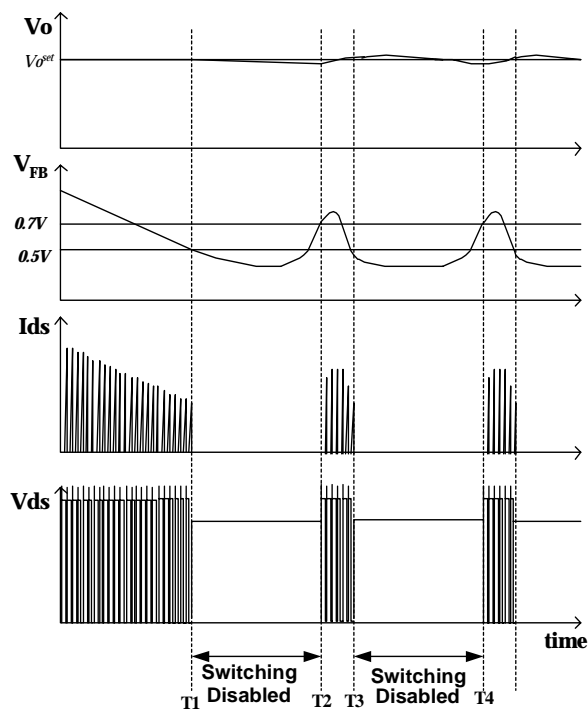


Figure 8. Waveforms of Burst Operation

Typical application circuit

| Application | Output Power | Input Voltage | Output Voltage (Max Current) |
|-------------|--------------|--------------------------------|------------------------------|
| LCD Monitor | 34W | Universal Input (85-265Vac) | 5V (2.0A) 12V (2.0A) |

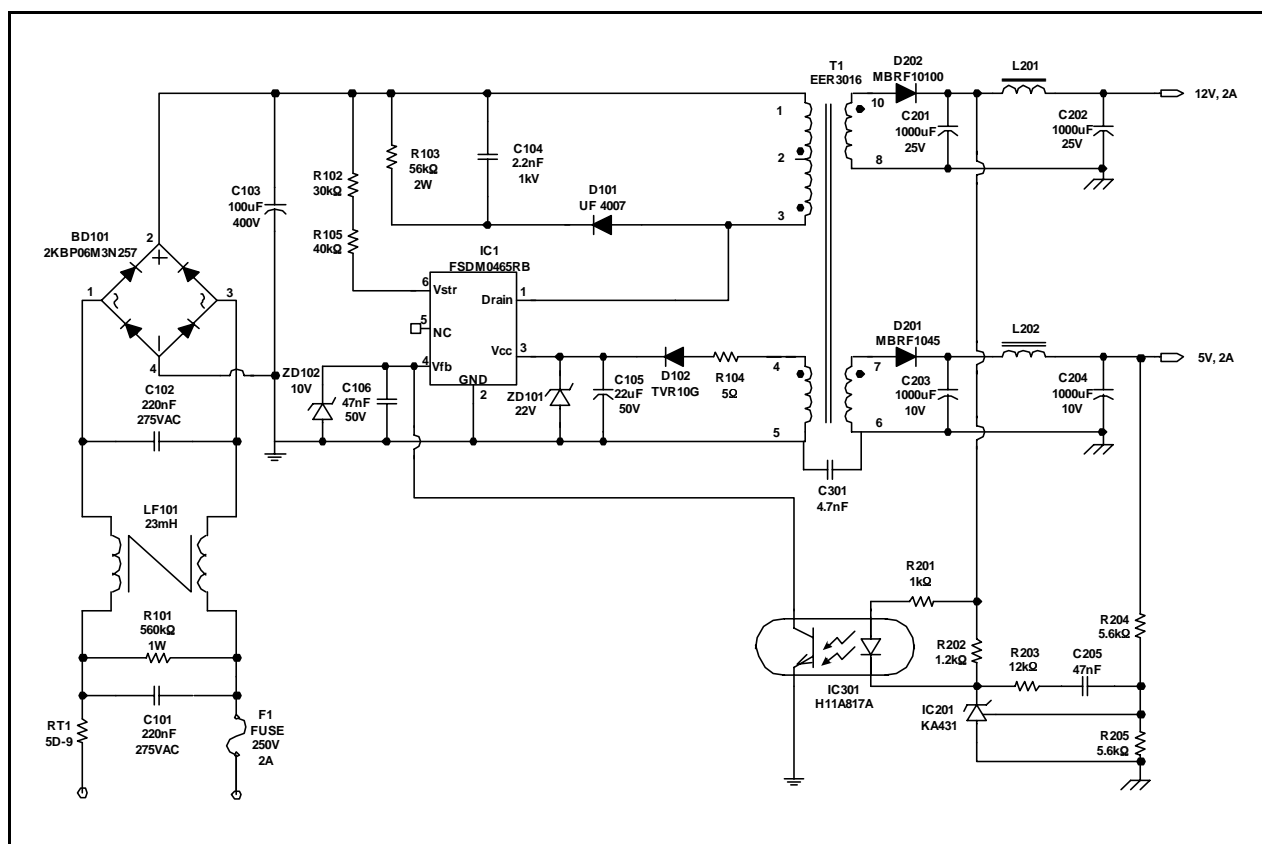
Features

- High efficiency (>81% at 85Vac input)
- Low zero load power consumption (<300mW at 240Vac input)
- Low standby mode power consumption (<800mW at 240Vac input and 0.3W load)
- Low component count
- Enhanced system reliability through various protection functions
- Internal soft-start (10ms)

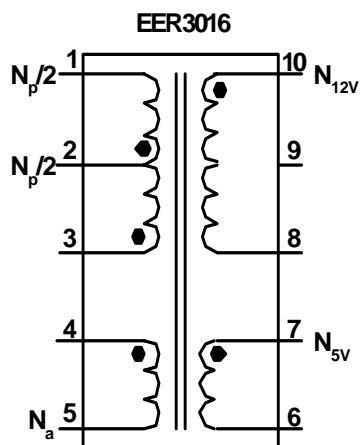
Key Design Notes

- Resistors R102 and R105 are employed to prevent start-up at low input voltage. After startup, there is no power loss in these resistors since the startup pin is internally disconnected after startup.
- The delay time for over load protection is designed to be about 50ms with C106 of 47nF. If a faster triggering of OLP is required, C106 can be reduced to 10nF.
- Zener diode ZD102 is used for a safety test such as UL. When the drain pin and feedback pin are shorted, the zener diode fails and remains short, which causes the fuse (F1) to blow and prevents explosion of the opto-coupler (IC301). This zener diode also increases the immunity against line surges.

1. Schematic



2. Transformer Schematic Diagram



3. Winding Specification

| No | Pin (s→f) | Wire | Turns | Winding Method |
|---|-----------|----------------------|-------|------------------|
| Na | 4 → 5 | 0.2 ^φ × 1 | 8 | Center Winding |
| Insulation: Polyester Tape t = 0.050mm, 2Layers | | | | |
| Np/2 | 2 → 1 | 0.4 ^φ × 1 | 18 | Solenoid Winding |
| Insulation: Polyester Tape t = 0.050mm, 2Layers | | | | |
| N12V | 10 → 8 | 0.3 ^φ × 3 | 7 | Center Winding |
| Insulation: Polyester Tape t = 0.050mm, 2Layers | | | | |
| N5V | 7 → 6 | 0.3 ^φ × 3 | 3 | Center Winding |
| Insulation: Polyester Tape t = 0.050mm, 2Layers | | | | |
| Np/2 | 3 → 2 | 0.4 ^φ × 1 | 18 | Solenoid Winding |
| Outer Insulation: Polyester Tape t = 0.050mm, 2Layers | | | | |

4. Electrical Characteristics

| | Pin | Specification | Remarks |
|--------------------|-------|---------------|---------------------------|
| Inductance | 1 - 3 | 650uH ± 10% | 100kHz, 1V |
| Leakage Inductance | 1 - 3 | 10uH Max | 2 nd All Short |

5. Core & Bobbin

Core: EER 3016

Bobbin: EER3016

Ae(mm²): 96

6.Demo Circuit Part List

| Part | Value | Note | Part | Value | Note |
|------------------|--------------|------------------------|---------------------|---------------|---------------------|
| Fuse | | | C301 | 4.7nF | Polyester Film Cap. |
| F101 | 2A/250V | | | | |
| NTC | | | Inductor | | |
| RT101 | 5D-9 | | L201 | 5uH | Wire 1.2mm |
| Resistor | | | L202 | 5uH | Wire 1.2mm |
| R101 | 560K | 1W | | | |
| R102 | 30K | 1/4W | | | |
| R103 | 56K | 2W | | | |
| R104 | 5 | 1/4W | Diode | | |
| R105 | 40K | 1/4W | D101 | UF4007 | |
| R201 | 1K | 1/4W | D102 | TVR10G | |
| R202 | 1.2K | 1/4W | D201 | MBRF1045 | |
| R203 | 12K | 1/4W | D202 | MBRF10100 | |
| R204 | 5.6K | 1/4W | ZD101 | Zener Diode | 22V |
| R205 | 5.6K | 1/4W | ZD102 | Zener Diode | 10V |
| | | | Bridge Diode | | |
| | | | BD101 | 2KBP06M 3N257 | Bridge Diode |
| Capacitor | | | Line Filter | | |
| C101 | 220nF/275VAC | Box Capacitor | Line Filter | | |
| C102 | 220nF/275VAC | Box Capacitor | LF101 | 23mH | Wire 0.4mm |
| C103 | 100uF/400V | Electrolytic Capacitor | IC | | |
| C104 | 2.2nF/1kV | Ceramic Capacitor | IC101 | FSDM0465RB | FPS™(4A,650V) |
| C105 | 22uF/50V | Electrolytic Capacitor | IC201 | KA431(TL431) | Voltage Reference |
| C106 | 47nF/50V | Ceramic Capacitor | IC301 | H11A817A | Opto-Coupler |
| C201 | 1000uF/25V | Electrolytic Capacitor | | | |
| C202 | 1000uF/25V | Electrolytic Capacitor | | | |
| C203 | 1000uF/10V | Electrolytic Capacitor | | | |
| C204 | 1000uF/10V | Electrolytic Capacitor | | | |
| C205 | 47nF/50V | Ceramic Capacitor | | | |

7. Layout

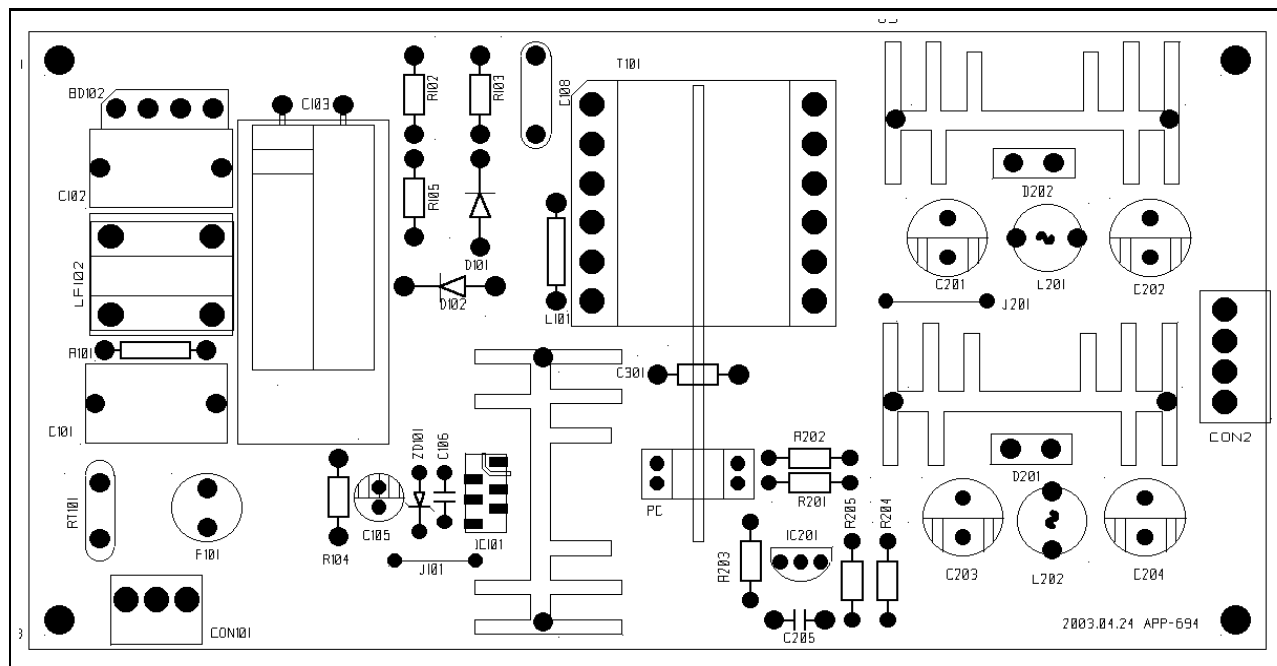


Figure 9. PCB Top Layout Considerations for FSDM0465RB

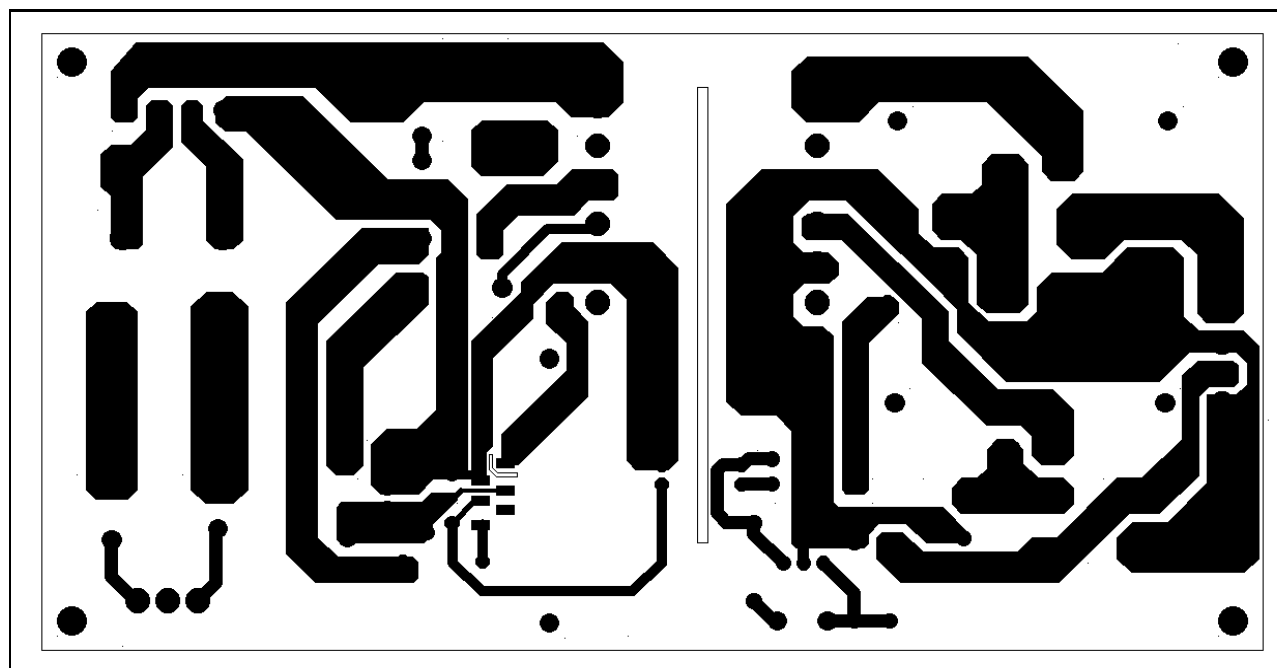
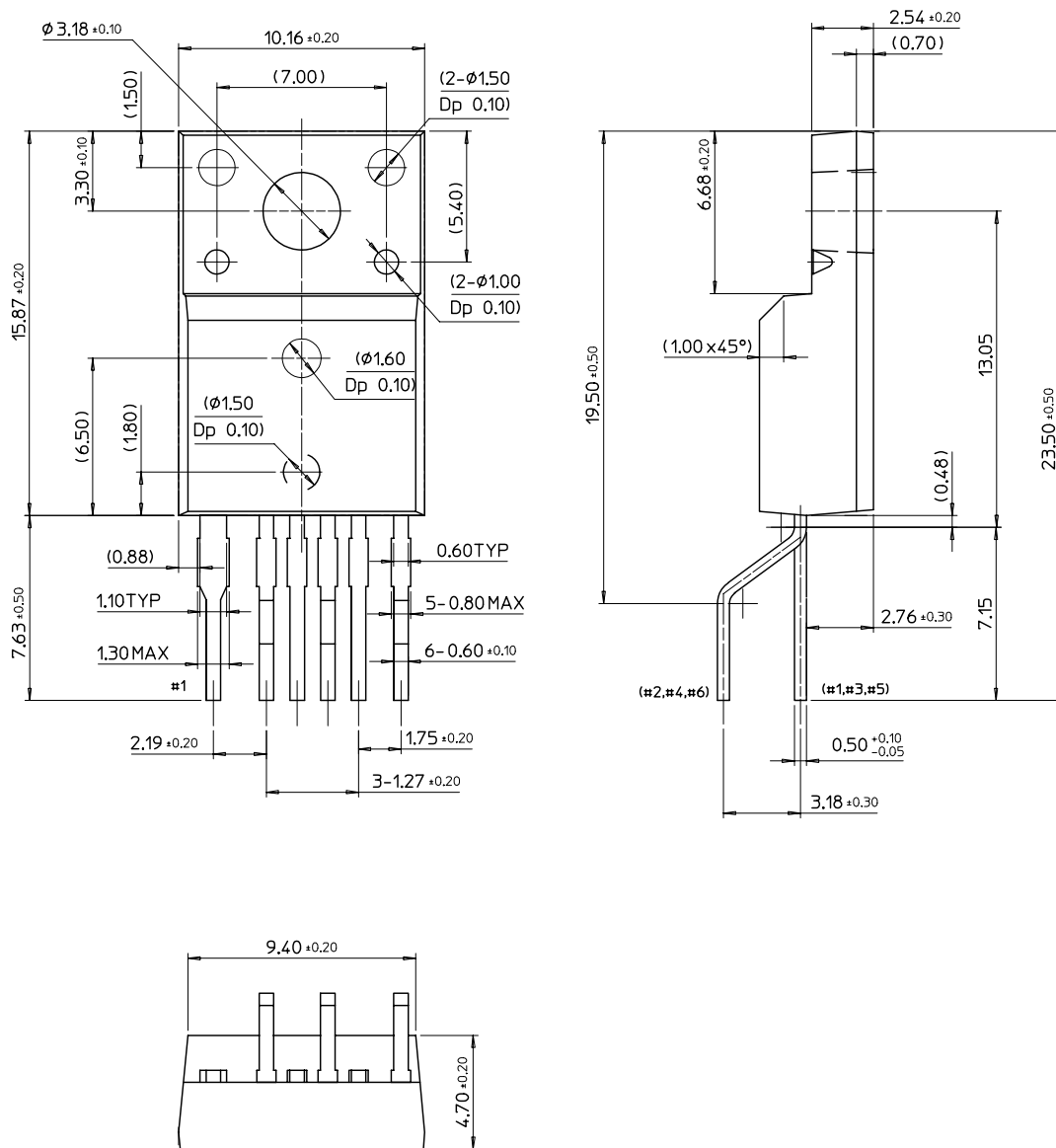


Figure 10. PCB Bottom Layout Considerations for FSDM0465RB

Package Dimensions

TO-220F-6L(Forming)



Ordering Information

| Product Number | Package | Marking Code | BVdss | Rds(on) Max. |
|----------------|---------------------|--------------|-------|--------------|
| FSDM0465RBWDTU | TO-220F-6L(Forming) | DM0465R | 650V | 2.6 Ω |

WDTU: Forming Type

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